

## SCIENTIFIC PROGRAM | TUESDAY, JULY 23

12:30-12:45	Crystal growth and investigations of the RAIX (R=Ce, Pr, X=Si, Ge) Weyl semimetals Daniel A. Mayoh (University of Warwick, UK)	
12:45-13:00	Single crystal growth of $Sr_2MCu_2Se_2O_2$ (M= Co, Ni, Zn) by melt-solidification method Takahiro Kato (Tokyo University of Science, Japan)	
13:00-13:15	Influence of growth conditions and stoichiometry on morphology and scintillation properties of GSAG:Ce single crystals Jan Pejchal (Czech Academy of Sciences, Czech Republic)	
13:15-13:30	Centimeter sized organic single crystal BNA with high quality for broadband terahertz generation Zixuan Jia (Northwestern Polytechnical University, China)	
13:30-13:45	Growth of Lithium Tantalate crystal from melt without precious-metal crucible under oxidizing atmosphere Taketoshi Tomida (Northwestern Polytechnical University, China)	
15:15-17:00 Chairs	<b>Session S1 - Fundamentals of Crystal Growth and Modeling</b> Dominique Maes, Janis Virbulis	Room 106
15:15-15:30	Analyzing the pattern formation on vicinal surfaces in diffusion-limited and kinetics-limited growth regimes: the effect of step-step exclusion Hristina Popova (Bulgarian Academy of Sciences, Bulgaria)	
15:30-15:45	Toward automatic control of the optical floating zone crystal growth process via machine learning Jeffrey Derby (University of Minnesota, USA)	
15:45-16:00	Surface dynamics - the driving force of the pattern formation Magdalena Zaluska-Kotur (Institute of Physics PAS, Poland)	
16:00-16:15	Potential channel – source of surface meanders Marta Chabowska (Institute of Physics PAS, Poland)	
16:15-16:30	Studying epitaxial growth kinetics by kinetic Monte Carlo simulations Wolfram Miller (Leibniz-Institut für Kristallzüchtung, Germany)	
16:30-16:45	ML-based Surrogate Model for Parameter Calibration and Uncertainty Analysis of Crystal Growth Simulations Lorenz Taucher (Montanuniversität Leoben, Austria)	
16:45-17:00	Modeling Fibrous discontinuous precipitation with the phase field technique: 2D and 3D simulations Lynda Amirouche (USTHB, Algeria)	
15:15-16:30 Chairs	<b>Session S2 - Semiconductor Single Crystals and Films</b> Alice Hospodková, Paweł Prystawko	Room 105
15:15-15:30	Liquid phase epitaxy of SiGe films using printing and firing Kohei Ito (Nagoya University, Japan)	
15:30-15:45	A new composite material consisting of MnTe matrix with embedded $MnBi_2Te_4$ quantum dots Paweł Skupiński (Institute of Physics PAS, Poland)	

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15:45-16:00	Defects studies on diamond Schottky barrier diode by Electron Beam Induced Current for beta-voltaic applications Manoël Jacquemin (DIAMFAB, France)	
16:00-16:15	Synthesis and characterization of BaZrS <sub>3</sub> thin films for photovoltaic applications using a stacked elemental layer methodology Sumbal Jamshaid (Friedrich-Alexander-Universität Erlangen-Nürnberg, Germany)	
16:15-16:30	Effect of aluminum doping on the structural and electrical properties of indium selenide single crystals Xuechao Liu (Shanghai Institute of Ceramics, China)	
16:30-16:45	Optimization Strategies for Polarization Doped p-type layers in InGaN Emitters Muhammed Aktas (Unipress, Poland)	
15:15-17:00 Chairs	<b>Session S11 - Bulk Crystal Growth</b> Dorota Pawlak, Piotr Piotrowski	Room 107
15:15-16:00 INVITED TALK	Steps dynamics and the growth of crystals and epitaxial layers Stanisław Krukowski (Unipress, Poland)	
16:00-16:15	Modeling of Convective Transport in Crystallization of Gallium Nitride by Basic Ammonothermal Method – transient changes of velocity and temperature Marek Żak (Unipress, Poland)	
16:15-16:30	Preparation of GaN Substrates: From Raw Crystals to Finished Products Mikołaj Amilusik (Unipress, Poland)	
16:30-16:45	Growth of high-purity 4H-SiC via conventionally PVT method and its limitations Jonas Ihle (Crystal Growth Lab, FAU Erlangen, Germany)	
16:45-17:00	Large sapphire crystal growth technology using controlled modified resistive Kyropoulos (KY) technique Nicolas Pruneau (ECM Greentech, France)	
17:00-19:00	<b>Poster Session II - Sessions S2, S8, S10 and S11</b>	Room 116